

19. A method according to any one of claims 1, 2, 9 and 10, wherein the crystallized semiconductor layer contains carbon at a concentration not higher than 5×10^{18} atoms/cm³.

20. A method according to any one of claims 1, 2, 9 and 10,
wherein the crystallized semiconductor layer contains oxygen at
a concentration not higher than 5×10^{19} atoms/cm³. --